CHEMICAL VAPOR DEPOSITION (CVD) OR PLASMA ENHANCED CVD OF SILICON OR TUNGSTEN CONTAINING FILMS IN A CVD CHAMBER.

FLUORINE BASED CLEANING PLASMA (IN SITU OR REMOTE) TO REMOVE DEPOSITS FROM THE INTERIOR SURFACES OF THE CVD CHAMBER.

IN SITU CLEANING PLASMA OF A HYDROGEN CONTAINING GAS AND AN OXYGEN CONTAINING GAS TO REMOVE FLUORINE RESIDES FROM THE INTERIOR SURFACES OF THE CVD CHAMBER.

Figure 1

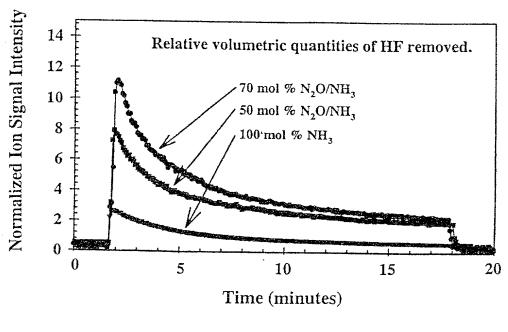


Figure 2

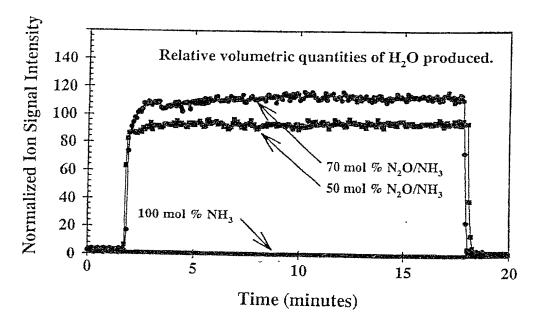


Figure 3

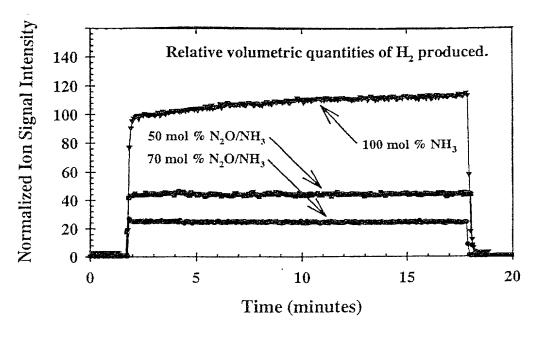


Figure 4

